

L Number	Hits	Search Text	DB	Time stamp
1	1325	(EVANS SAME DAVID) OR (HSU SAME (SHENG OR TENG)) OR (ULRICH SAME BRUCE) OR (TWEET SAME DOUGLAS)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12 17:54
2	1325	(EVANS SAME DAVID) OR (HSU SAME (SHENG OR TENG)) OR (ULRICH SAME BRUCE) OR (TWEET SAME DOUGLAS) OR (STECKER SAME LISA)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12 17:56
3	98	((EVANS SAME DAVID) OR (HSU SAME (SHENG OR TENG)) OR (ULRICH SAME BRUCE) OR (TWEET SAME DOUGLAS) OR (STECKER SAME LISA)) AND CMOS	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12 17:56
4	37	((EVANS SAME DAVID) OR (HSU SAME (SHENG OR TENG)) OR (ULRICH SAME BRUCE) OR (TWEET SAME DOUGLAS) OR (STECKER SAME LISA)) AND CMOS) and (sti or (shallow adj trench adj isolation) or (trench same isolation))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12 17:57
5	19	((EVANS SAME DAVID) OR (HSU SAME (SHENG OR TENG)) OR (ULRICH SAME BRUCE) OR (TWEET SAME DOUGLAS) OR (STECKER SAME LISA)) AND CMOS) and (sti or (shallow adj trench adj isolation) or (trench same isolation)) and polysilicon and (cmp or (chemical adj mechanical\$2 adj planariz\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12 17:58
6	15	((EVANS SAME DAVID) OR (HSU SAME (SHENG OR TENG)) OR (ULRICH SAME BRUCE) OR (TWEET SAME DOUGLAS) OR (STECKER SAME LISA)) AND CMOS) and (sti or (shallow adj trench adj isolation) or (trench same isolation)) and polysilicon and (cmp or (chemical adj mechanical\$2 adj planariz\$5)) and (thickness or thick) and (depth or deep)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12 17:58
-	2961	((438/207) or (438/218) or (438/219) or (438/221) or (438/401) or (438/404) or (438/424)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12 16:27
-	660	((438/207) or (438/218) or (438/219) or (438/221) or (438/401) or (438/404) or (438/424)).CCLS.) and (cmos or (complementary adj metal adj oxide adj semiconductor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12 16:29
-	459	((438/207) or (438/218) or (438/219) or (438/221) or (438/401) or (438/404) or (438/424)).CCLS.) and (cmos or (complementary adj metal adj oxide adj semiconductor)) and ((trench same isolation) or (shallow adj trench adj isolation) or sti)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12 16:31
-	432	((438/207) or (438/218) or (438/219) or (438/221) or (438/401) or (438/404) or (438/424)).CCLS.) and (cmos or (complementary adj metal adj oxide adj semiconductor)) and polysilicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12 16:31
-	309	((438/207) or (438/218) or (438/219) or (438/221) or (438/401) or (438/404) or (438/424)).CCLS.) and (cmos or (complementary adj metal adj oxide adj semiconductor)) and polysilicon and ((trench same isolation) or (shallow adj trench adj isolation) or sti)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12 16:31

238	((((438/207) or (438/218) or (438/219) or (438/221) or (438/401) or (438/404) or (438/424)).CCLS.) and (cmos or (complementary adj metal adj oxide adj semiconductor))) and polysilicon) and ((trench same isolation) or (shallow ajd trench adj isolation) or sti)) and (thickness or thick) and (depth or deep)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12 16:33
103	((((438/207) or (438/218) or (438/219) or (438/221) or (438/401) or (438/404) or (438/424)).CCLS.) and (cmos or (complementary adj metal adj oxide adj semiconductor))) and polysilicon) and ((trench same isolation) or (shallow ajd trench adj isolation) or sti)) and (thickness or thick) and (depth or deep)) and (cmp or (chemical adj mechanical\$2 adj planariz\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12 16:38
9	((((438/207) or (438/218) or (438/219) or (438/221) or (438/401) or (438/404) or (438/424)).CCLS.) and (cmos or (complementary adj metal adj oxide adj semiconductor))) and polysilicon) and ((trench same isolation) or (shallow ajd trench adj isolation) or sti)) and (thickness or thick) and (depth or deep)) and (cmp or (chemical adj mechanical\$2 adj planariz\$5)) and (alignment same (mark\$3 or key))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12 17:51